Colloquium: Spintronics in graphene and other two-dimensional materials

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After the first unequivocal demonstration of spin transport in graphene, surprisingly working at room temperature (Tombros et al., 2007), it was quickly realised the relevance of this then recently discovered material, for both fundamental spintronics and future applications. Over the last decade, exciting results have made the field of graphene spintronics to blossom and evolve to a next generation of studies extending to new two-dimensional (2D) compounds. This Colloquium reviews recent theoretical and experimental advances in studies of electronic spin transport in graphene and related 2D materials, focusing on the new perspectives provided by heterostructures thereof and their emergent phenomena, including proximity-enabled spin-orbit effects, coupling spin to light, electrical tunability and 2D magnetism. We conclude by listing current challenges and promising research directions.

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I. INTRODUCTION

Since the discovery of graphene, the field of two-dimensional (2D) materials have become one of the hot topics in solid state physics, mainly because of their prominent mechanical, optical, electrical and magnetic properties (Castro Neto et al., 2009). High electronic charge mobility, low spin orbit coupling strength, negligible hyperfine interaction and gate tunability, are part
of the properties which have established graphene also as an emerging material for spintronics (Tombros et al., 2007). As a clear example, graphene exhibits the longest spin relaxation length ever measured at room temperature (Drögelet al., 2016; Inglia-Aynés et al., 2015). This is important since the property of long-distance spin communication (Gebebe et al., 2019; Kamalakar et al., 2015) enables the transmission and manipulation of spin signals within complex multi-terminal device architectures. Recently, the field has moved beyond graphene, towards exploring the properties of other 2D crystals, including recently discovered ones, in particular for investigating proximity interactions in their van der Waals heterostructures. The latter serves as a testbed for inducing gating proximity interactions in their van der Waals heterostructures. The former serves as a testbed for inducing new emergent functionalities, by compensating for any weaknesses associated to any of the individual layers and therefore enabling novel spintronics research. Moreover, the observation of long spin relaxation lengths (Drögelet al., 2016) together with spin-charge conversion (Saefet al., 2019) and spin manipulation (Avsar et al., 2017a) capabilities in van der Waals heterostructures make 2D crystals appealing material systems for the development of low-power spintronics, including devices based on tunnel magnetoresistance (Kim et al., 2018), spin-transfer torque (Lin et al., 2013), XOR spin logic gates (Wen et al., 2016) and ultimately all-spin logic with built-in memory (Behin-Aein et al., 2010).

Given the increasing effort on the search for new spintronics phenomena in 2D materials, there is a present need for a review and critical discussion of recent experimental and theoretical progress within the field of 2D spintronics. We note there are relevant reviews on spin transport (Chappet et al., 2007; Meservey and Tedrow, 1994; Wolf et al., 2006; Žutić et al., 2004), graphene (Castro Neto et al., 2009; Das Sarma et al., 2011; Peres, 2010), and graphene spintronics (Garcia et al., 2018; Gurram et al., 2018; Han et al., 2012; Pesin and MacDonald, 2012; Roche and Valenzuela, 2014; Seneor et al., 2012; Shiraiishi, 2012). Our aim in this review is to offer a broad and balanced coverage, starting with an introduction to fundamentals for those new to the fields of spintronics and graphene, while encompassing critical discussions that address recent advances and point to challenges and future directions in this vibrant field. While brief discussions on chemically modified graphene and alternative spin injection schemes will be also provided, this colloquium primarily focuses on electronic spin transport in pristine 2D materials and novel devices based on their heterostructures.

A. Initial spin transport experiments

In 1988, A. Fert and P. Grunberg independently discovered that the resistance of ferromagnetic/non-magnetic (FM/NM) metallic multilayer structures depends on the relative orientation of the FM layers (Baibich et al., 1988; Binash et al., 1989). This discovery, termed giant magnetoresistance (GMR), was later utilized in the magnetic field sensors of hard disk drives (Tsang et al., 1998), constituting the first major application of spintronics within modern electronics. The physics behind this achievement has formed the foundation of spin transport experiments and their evolution over the last three decades.

At the heart of most spin transport phenomena is the creation of spin accumulation in a NM material. The latter can be electrically induced by applying a charge current to the NM via a FM contact. The injected spin information propagates throughout the NM as a spin current, which can be detected using a second FM contact. Such detection is possible as long as the separation between the injector and detector contacts is less than the characteristic length on which the non-equilibrium spin information relaxes. Within these conditions, the resistance of the device depends on the relative magnetization direction of the injector and detector contacts, which is detected as a resistance switch when their relative orientation changes from parallel to the antiparallel (Jedema et al., 2001; Johnson and Silsbee, 1985). Such a spin valve signal in FM/NM/FM structures is therefore utilized for the realization of spin injection, spin transport and spin detection. In this local architecture, the charge and spin currents are co-located within the same NM channel. The measured signal is therefore a combination of a spin-dependent resistance, representative of the spin transport, and a spin-independent resistance, purely associated to the charge transport. Since the ratio of the spin-dependent resistance to the spin-independent resistance is generally small, and charge-based phenomena can mimic the spin signal under study, this two-terminal measurement geometry is not ideal for probing spin-dependent transport.

Multi-terminal measurement geometries are thus favoured for the unambiguous study of spin-dependent transport (Fig. 1). One alternative is the three-terminal Hanle geometry, where a single magnetic contact is used to create and detect spin accumulation. The latter is evidenced by the modulation of the contact resistance due to the spin precession effect of an applied magnetic field. This measurement configuration has advantages for probing spin lifetimes in highly-resistive channel materials or in materials with a short spin relaxation length, and has been utilized to detect spin injection in GaAs (Lou et al., 2006, 2007), Si (Dash et al., 2009) and Ge (Jeon et al., 2011). However, a disadvantage of this configuration is that the same contact is used to electrically inject and detect the spin information, which does not fully solve the issue of mixing charge and spin phenomena, as evidenced in measurements showing spin accumulations that are inconsistent with the theoretical expectations (Tran et al., 2009). Therefore, the ideal method is that
Measurement configurations and spin transport in graphene. (a) Four-terminal nonlocal \( (V_{NL}) \), three-terminal Hanle \( (V_{3T}) \) and two-terminal local \( (V_{2T}) \) measurement geometries. Ferromagnetic (FM) contacts are used to inject and detect spins in a non-magnetic (NM) channel via a tunnel barrier (TB). The bottom cartoon illustrates a top-view of spin precession under an out-of-plane applied magnetic field \( B \). (b) Scanning electron micrograph of the first non-local graphene spin valve device. (c) Non-local spin valve signal in monolayer graphene. Vertical arrows represent the polarization direction of the contacts, lateral arrows represent the magnetic field sweep direction. (d) Corresponding Hanle spin precession signal, for parallel orientation of the contacts. Adapted from Tombros et al. (2007).

FIG. 1 Measurement configurations and spin transport in graphene. (a) Four-terminal nonlocal \( (V_{NL}) \), three-terminal Hanle \( (V_{3T}) \) and two-terminal local \( (V_{2T}) \) measurement geometries. Ferromagnetic (FM) contacts are used to inject and detect spins in a non-magnetic (NM) channel via a tunnel barrier (TB). The bottom cartoon illustrates a top-view of spin precession under an out-of-plane applied magnetic field \( B \). (b) Scanning electron micrograph of the first non-local graphene spin valve device. (c) Non-local spin valve signal in monolayer graphene. Vertical arrows represent the polarization direction of the contacts, lateral arrows represent the magnetic field sweep direction. (d) Corresponding Hanle spin precession signal, for parallel orientation of the contacts. Adapted from Tombros et al. (2007).

Quantitative extraction of the parameters that control spin transport in a diffusive channel, namely the spin relaxation time \( \tau_s \) and the spin diffusion coefficient \( D_s \), can be achieved by measuring the dependence of the spin signal on the separation between injector and detector electrodes. The observed decay with increasing separation yields the spin relaxation length, \( \lambda_s = \sqrt{D_S \tau_s} \), while \( D_s \) can be calculated from the resistivity via the Einstein relation (Jedema et al., 2001). Nevertheless, this requires the study of multiple devices with different separation and is sensitive to the reproducibility of other parameters, like the spin injection efficiency of the contacts, which also control the magnitude of the spin signal. Hanle spin precession is an alternative measurement based on studying the dependence of the spin signal on an applied magnetic field \( B \) perpendicular to the orientation of the injected spin (Jedema et al., 2002b). Here, a torque is exerted on the electron spin, which is forced to precess at the Larmor frequency, as sketched in Fig. 1(a). In a fully coherent 1D channel the spin precession would lead to an oscillatory response as a function of \( B \). Nevertheless, in a diffusive 2D or 3D channel each electron spin follows a different path towards the detector, due to momentum scattering, with each one having a different transit time and therefore a different precession angle, causing dephasing in the net spin accumulation. Furthermore the spin accumulation relaxes back to its equilibrium value. The combined effect of spin dephasing and relaxation, controlled by \( D_s \) and \( \tau_s \), determine the response of the spin signal as a function of \( B \), as shown in Fig. 1(d). This powerful technique removes the requirement to study multiple devices to extract spin parameters, as it relies on fitting the lineshape of the response only based on the two fundamental parameters controlling spin transport (Jedema et al., 2002a). Hanle spin precession is the golden standard for the unambiguous demonstration of spin transport using a four-terminal non-local geometry and it has been extensively applied to metallic (Jedema et al., 2002b), semiconducting (Lou et al., 2007) and graphene (Maassen et al., 2012; Popinciuc et al., 2009) spin channels.

Spin transport experiments in graphene have utilized the measurement techniques described above. The first report on spin transport demonstrated a hysteretic magneto-transport response with a 10% change in resistance by utilizing a two-terminal local geometry (Hill et al., 2006). Shortly after, Tombros et al. (2007) un-
equivocally demonstrated room-temperature spin transport with micrometer-long spin relaxation lengths in monolayer graphene, by employing a tunnel barrier for efficient spin injection and measuring in a four-terminal non-local geometry. This measurement configuration then became the standard method to characterize the distinct spin transport properties of graphene, as demonstrated by Cho et al. (2007) and Popinciuc et al. (2009) who modulated spin transport in graphene via the application of vertical electric fields. On the other hand, application of lateral electric fields also demonstrated to produce spin drift and therefore modulate spin injection efficiencies (Józsa et al., 2008, 2009b).

After the characterization of basic spin transport properties of graphene fabricated on standard Si/SiO$_2$ substrates, Józsa et al. (2009a) examined the dominant spin relaxation mechanism for the first time by studying the relation between momentum and spin relaxation times in monolayer graphene. A further discussion on spin relaxation is presented in Section IIIA. Initial devices also demonstrated the capability to achieve robust spin polarization in mono and multi-layer graphene, by demonstrating a linear dependence of non-local voltage on injected current up to 10 mA (Muramoto et al., 2009; Shiraiishi et al., 2009). Such superior spin injection properties, in comparison with previous semiconductor-based devices, is a result of the transport properties of graphene and the suppression of any significant interface spin scattering, as later confirmed by the observation of identical spin transport parameters in graphene spin valve devices measured with either three and four-terminal techniques over a wide range of temperatures (Dankert et al., 2014b).

**B. Fundamentals of spin-orbit coupling in 2D crystals**

In the solid state electrons usually move much slower than light, with a speed $v \ll c$. However, relativistic corrections are not completely negligible, representing both a major limitation to spin transport and a source of opportunities for spin injection, manipulation and detection. The leading correction in $v/c$ is provided by the Hamiltonian

$$H_{\text{SO}} = \frac{1}{2m^2c^2} (\nabla V \times \mathbf{p}) \cdot \mathbf{s}, \quad (1)$$

where $m$ is the electron mass and $\mathbf{p}$ and $\mathbf{s} = (s_x, s_y, s_z)$ represent the linear momentum and spin operators, respectively. In a solid, $V$ is just the crystalline potential. As a first approximation, we can consider an atomic insulator, where electrons are bound to the nuclei of the constituents of the solid by a hydrogen-like potential of the form $V(r) \propto Z/r$, $Z$ being the atomic number. Eq. (1) can be written as $H_{\text{SO}} = \Delta_{\text{SO}} \mathbf{L} \cdot \mathbf{s}$, where $\mathbf{L} = \mathbf{r} \times \mathbf{p}$ is the angular momentum operator and $\Delta_{\text{SO}} \propto Z/r^3$. The averaged *intra-atomic* spin-orbit coupling (SOC) is dominated by electrons close to the nucleus, at distances of the order of the Bohr radius, $r \sim a_B \propto Z^{-1}$, for which the nuclear field remains almost unscreened. Since the probability of finding an electron near the nucleus scales as $\sim Z^{-2}$ (Landau and Lifshitz, 1977), the intra-atomic SOC constant goes like $\Delta_{\text{SO}} \propto Z^2$; the heavier the atom, the larger the relativistic effect. In fact, the fast decay of the spin-orbit interaction with the distance to the nucleus justifies a tight-binding description. For the same reasons, relativistic corrections are smaller for bands built up from higher atomic orbitals.

The spin quantum number reflects the way that the electronic wave function transforms under rotations. Hence, the point group of the lattice (the set of proper and improper rotations that leave invariant the crystal structure) has a strong influence on the relativistic corrections to the electronic bands. The basis of Bloch states around high-symmetry points of the Brillouin zone must be adapted to the irreducible representations of the so-called *double group* (Dresselhaus et al., 2008), consisting of the original symmetry operations plus the rotation by $2\pi$ along one of the principal axis of the crystal that defines the natural spin quantization. For 2D materials, this is usually the axis perpendicular to the plane of the crystal. The bands are described in terms of the direct product $\Gamma \times D_{1/2}$, where $\Gamma$ labels the irreducible representation associated with the orbital part of the wave function, and $D_{1/2}$ is the spinor representation generated by Pauli matrices $s_i$. This group-theory approach can be simplified in practice. Typically, the strength of the spin-orbit interaction is much weaker than the energy separation between states labeled by different angular-momentum numbers. Therefore, the main orbital character of the bands does not change much, and the indices associated with the irreducible representations of the original point group are still good quantum numbers.

Improper rotations play a crucial role given the pseudovectorial nature of the spin operator. If the crystal structure possesses a complete center of inversion, then the original two-fold degeneracy of the bands is preserved. Otherwise, the bands are spin-split except at time-reversal symmetric points. Nevertheless, a plane of inversion always protects the perpendicular projection of the spin close to high-symmetry points. Graphene is mirror symmetric, meaning that $s_z$ is still a good quantum number in the low-energy limit even in the presence of relativistic interactions. Moreover, in non-centrosymmetric materials with mirror symmetry, like transition-metal dichalcogenides (TMDC), the large spin-splittings of the bands provide a strong protection of $s_z$ against external perturbations.

Despite the small atomic number of carbon, the effect of relativistic interactions in the spectrum of its different allotropes is a subject of intensive research. The spin-orbit coupling in graphite was first analyzed in the pioneering works by Słonczewski (Słonczewski and
et al. (1958) and Dresselhaus (Dresselhaus and Dresselhaus, 1965). In the next section we focus on single and few layer graphene allotropes and TMDCs, describing how SOC can be exploited in spintronic devices.

II. STATE OF THE ART IN GRAPHENE SPINTRONICS

A. Spin–orbit coupling in graphene

Graphene consists of a single layer of sp² hybridized carbon atoms (Castro Neto et al., 2009; Katsnelson, 2007). In-plane \( p_{x,y} \) and \( s \) orbitals participate in the strong \( \sigma \)-bonds that keep carbon atoms covalently attached, forming a trigonal planar structure with a distance between atoms of \( a = 1.42 \) Å. The remaining electron occupying the \( p_z \) orbital is free to hop between neighboring sites, leading to the \( \pi \) bands responsible for the conductive properties. The low-energy \( \pi \) bands are parabolic, whereas the \( \sigma \) bands are flat.

The minimal microscopic model that captures spin-orbit effects should include at least both \( \pi \) and \( \sigma \) orbitals. In this model, the intrinsic SOC arises from virtual transitions into \( \sigma \) states mediated by the intra-atomic spin-orbit interaction, flipping the spin. Perturbation theory gives the effective hopping (Huertas-Hernando et al., 2006; Konschuh et al., 2006; Min et al., 2006)

\[
\Delta_{KM} = \frac{\epsilon_s \Delta_{SO}^2}{18 V_{sp}^2} \approx 1 \text{ meV},
\]

where \( V_{sp} \approx 4.2 \text{ eV} \) represents the hopping between \( p_{x,y} \) and \( s \) orbitals, \( \epsilon_s \approx -7.3 \text{ eV} \) is the energy of the latter measured with respect to the intrinsic Fermi level (Tománek and Louie, 1988) and the intra-atomic spin-orbit coupling for carbon is \( \Delta_{SO} \approx 7.86 \text{ meV} \). This second-order effect is exceeded by the contribution from the hybridization with higher-energy \( d \) orbitals (Slonczewski and Weiss, 1958), leading to \( \Delta_{KM} \approx 12 \text{ meV} \).

The Bychkov-Rashba term in the second line of Eq. (2) removes the spin degeneracy of the bands and tends to close the intrinsic spin-orbit gap. As we mentioned before, it is naturally present when the mirror symmetry is broken while the planar \( C_6 \) symmetry is preserved. A handy example is the case of an electric field perpendicular to the graphene sample. A dipolar coupling of the form \( \mathcal{H}_d = e \mathcal{E}_z \cdot \hat{z} \) induces transitions between \( p_z \) and \( s \) orbitals parametrized by \( \zeta \equiv \langle s | \hat{z} | p_z \rangle \). The electron goes back to the \( \pi \) band through the intra-atomic spin-orbit interaction, flipping the spin. Perturbation theory gives

\[
\Delta_{BR} = \frac{\epsilon_s \zeta \Delta_{SO}}{3 V_{sp}} \approx 0.1 \text{ meV} \times \mathcal{E}_z [\text{V/nm}],
\]

where we have taken \( \zeta = 3 a_B \) for the numerical estimation. *Ab initio* calculations lower this estimate by an order of magnitude (Gmitra et al., 2009; Konschuh et al., 2010). Fig. 3 shows the different band topologies...
resulting from the competition between the intrinsic and Bychkov-Rashba SOC terms.

1. hBN-Gr: Long-distance spin transport

As a result of the small intrinsic spin-orbit coupling it was expected that graphene would exhibit a long-distance spin transport. This is evident when combining graphene with hexagonal boron nitride (hBN). Due to hBN’s reduced trapped charge concentration and atomically flat surface compared to conventional SiO\(_2\), hBN has been employed as an ideal substrate for boosting the electronic charge quality of graphene (Dean et al., 2010). Recently, hBN has been adapted in graphene spin valves as substrate (Zomer et al., 2012), encapsulating layer (Avsar et al., 2016; Guimarães et al., 2014; Gurram et al., 2016; Ingla-Aynés et al., 2015) and tunnel barrier (Kamalakar et al., 2014; Singh et al., 2016; Yamaguchi et al., 2013) to improve its spin transport properties and realize new device concepts.

The first single layer graphene-based spin valves fabricated on a hBN substrate demonstrated 20 \(\mu\)m distance spin transport, due to improved spin diffusion coefficient and high electronic mobility, see Fig. 4(a) (Zomer et al., 2012). Surprisingly, spin relaxation times obtained in these devices exhibited comparable values to those obtained on conventional SiO\(_2\) substrate. This observation was attributed to spin scattering due to fabrication-related residues, and motivated pursuing new studies including hBN encapsulation. Improved spin relaxation times up to 2 ns with spin relaxation lengths exceeding 12 \(\mu\)m were observed in partially encapsulated graphene (Guimarães et al., 2014). This device structure also allows studying the Rashba spin-orbit coupling and the resulting anisotropy of the spin relaxation time for spins pointing out-of-plane to spins pointing in-plane, and its modulation via perpendicular electric field, see Fig. 4(b).

A similar geometry was also employed for bilayer spin valve devices, leading to spin relaxation lengths of 24 \(\mu\)m (Ingla-Aynés et al., 2015). Avsar et al. (2016) performed a comparative study by discussing the effect of the substrate and polymer residues on spin transport, where the observation of similar spin transport characteristics in non-encapsulated graphene on SiO\(_2\) and hBN substrates suggested that spin transport in these devices was not limited by contacts, substrate phonons or impurities.

On the other hand, observation of a five-fold enhancement in spin relaxation times upon encapsulation, and a non-monotonic carrier concentration dependence of spin relaxation times, suggested that resonant scattering by unintentional magnetic impurities is the limiting source for spin scattering in graphene, consistent with a recent theoretical proposal (Kochan et al., 2015). These studies suggest that adapting a full encapsulation process could allow approaching graphene’s intrinsic spin transport performance. Towards this, Drögeler et al. (2016) developed a bottom-up approach for fabricating polymer free spin valves, where hBN encapsulated graphene was transferred on top of pre-fabricated Co/MgO spin electrodes. They observed record spin relaxation times of 12 ns with spin relaxation lengths exceeding 30 \(\mu\)m, despite the presence of pin-holes in their MgO tunnel barriers, as shown in Fig. 4(c). These results also confirm the relevance of polymer residues on enhancing spin scattering events.

2. Bilayer and few-layer graphene

In bilayer graphene the unit cell contains 4 atoms. In the conventional Bernal stacking the low-energy bands are built up from \(p_z\) orbitals localized at opposite sublattices in different layers. The bands touch at the corners of the Brillouin zone, as in the case of graphene, but with an approximately quadratic dispersion instead (McCann and Fal’ko, 2006). This degeneracy is protected by the \(D_{3d}\) point group symmetry of the crystal but it can be removed by applying a perpendicular electric field (Castro et al., 2007). Since the bands are quadratic, we must consider spin-orbit couplings up to linear order in crystal momentum. Within the 2-bands effective model, the intrinsic terms compatible with the crystallographic symmetries read (van Gelderen and Smith, 2010; Guinea,
FIG. 4 High Quality Heterostructures for Spin Transport. (a) Hanle spin precession measurement for a distance between injector and detector of 18 µm. From Zomer et al. (2012). (b) Electric field dependence of the ratio in- and out-of-plane injected spins at fixed carrier concentrations. Inset shows the optical picture of a completed device. From Guimarães et al. (2014). (c) Back gate voltage dependence of spin relaxation length in an inverted graphene spin valve. Inset shows the device schematics. From Drögeler et al. (2016).

\[ H_{so}^{blg} = \Delta_{KM} \sigma_z T_z s_z + \Delta_{BR} (k_x s_y - k_y s_x) \sigma_z. \] (5)

The first term is a Kane-Mele coupling, whereas the second adopts the form of the usual Bychkov-Rashba coupling in the 2D electron gas, \( k_x s_y - k_y s_x \), but with opposite sign for electrons residing at different layers/sublattices. Notice that this term does not remove the spin degeneracy since the unit cell possesses a complete center of inversion (\( D_{3d} = D_3 \times i \), where \( i \) is the inversion group). Another difference with respect to the case of single-layer graphene is that the Kane-Mele coupling is linear in the intra-atomic spin-orbit coupling due to the non-zero hybridization between \( \pi \) and \( \sigma \) orbitals localized at different layers.

Ab initio calculations give \( \Delta_{KM} = 12 \) µeV, \( \Delta_{BR} = 19 \) µeV·nm (Konschuh et al., 2012). The low-energy bands of bilayer graphene are shown in Fig. 5.

This symmetry-based analysis can be extended to graphene multilayers with an arbitrary number of layers \( N \) (Guinea et al., 2006; Mañes et al., 2007; Partoens and Peeters, 2006). The electronic properties of these systems depend both on \( N \) and the type of stacking. A Bernal stack with even \( N \) possesses \( D_{3d} \) symmetry. The low-energy bands can be seen as \( N/2 \) copies of the low-energy model of bilayer graphene. When \( N \) is odd, however, the point group of the crystal is \( D_{3h} \). In the simplest description, an additional band with linear (Dirac) dispersion appears, but none of these degeneracies is protected by the crystallographic symmetries in this case. The low-energy spectrum of rhombohedral stacks does not depend on the parity of the number of layers. There are only two bands that touch at corners of the Brillouin zone with dispersion \( |k|^N \). These bands become surface states localized at the top and bottom layers in the limit \( N \to \infty \). The remaining \( 2N - 2 \) bands form Dirac crossings protected by \( D_{3h} \) symmetry. Within the lowest-energy bands of centrosymmetric stacks only a Kane-Mele coupling is allowed by symmetry at \( k = 0 \) (with the sublattice operators properly defined), whereas in the case of non-centrosymmetric stacks the spin-orbit coupling removes the spin degeneracy (McCann and Koshino, 2010). However, the spin polarization along the out-of-plane direction is still a good quantum number due to mirror symmetry.

FIG. 5 Low-energy bands of bilayer graphene. a) Parabolic dispersion of the low-energy bands around one of the inequivalent corners of the Brillouin zone. The bands localized at the carbon atoms sitting on top of each other appear at higher energies, of the order of the inter-layer hopping \( \gamma_1 = 0.34 \) eV. b) The two parabolas overlap due to the trigonal warping of the bands, controlled by the other two inter-layer hopping parameters in the Slonczewski-Weiss-McClure parametrization, \( \gamma_3 = 0.28 \) eV and \( \gamma_4 = -0.14 \) eV. c) The SOC terms \( \Delta_{KM} = 12 \) µeV and \( \Delta_{BR} = 19 \) µeV·nm (Konschuh et al., 2012) lift the band crossings. Note that the bands remain spin degenerate due to inversion symmetry.
metry \((D_{3h} = D_3 \times \sigma_h)\), where \(\sigma_h\) is the mirror reflection along the basal plane).

3. The original Topological insulator

Despite its weakness, the spin-orbit coupling in graphene has attracted a lot of attention in the recent years due to the connection with the field of topological insulators (Hasan and Kane, 2010; Qi and Zhang, 2011). The intrinsic or Kane-Mele term removes the degeneracy at the Dirac points, opening a gap in the spectrum. Moreover, the virtual processes mediated by high energy bands resemble the pattern of complex hoppings proposed by Haldane as a model for the quantum anomalous Hall effect (Haldane, 1988). In this case, the phase \(\pm \pi/2\) accumulated by the wave function is opposite for spin up and down. In a finite geometry, chiral modes localized at the edges of the system appear within the bulk gap, as shown in the calculation of Fig. 2. Backscattering between counter-propagating modes with opposite spin polarization is forbidden by time-reversal symmetry (Kane and Mele, 2005a; Moore and Balents, 2007; Roy, 2009). This quantum spin-Hall effect is unobservable in practice due to the narrowness of the topological gap. Nevertheless, it has been theorized that it could be stabilized by heavy adatom deposition (Weeks et al., 2011).

The low SOC strength of graphene is detrimental for the implementation of graphene into many spintronics applications requiring high SOC strength such as spin FETs etc (Datta and Das, 1990). Moreover, it also restricts the realization of theoretically predicted quantum spin Hall state at experimentally accessible temperatures (Kane and Mele, 2005b). All these stimulate the development of new methods for extrinsically enhancing SOC.

B. Corrugations and resonant impurities

Corrugations naturally break the mirror symmetry of graphene, giving rise to new SOC terms. Microscopically, the origin of these new couplings is the change of relative orientation of the orbitals due to the extrinsic curvature (i.e., the bending) of the graphene sheet, which hybridizes the \(\pi\) and \(\sigma\) bands (otherwise, hopping between these orbitals would be precluded by mirror symmetry). In a low-energy continuum description, this extrinsic curvature is characterized by a second rank tensor, \(\mathbf{F}_{ij} \approx \partial_i \partial_j h\) with \(i, j = x, y\), describing the embedding of the graphene sheet in ambient space, where the field \(h(x, y)\) represents the out-of-plane displacement of carbon atoms at position \((x, y)\). The mean curvature \(\mathbf{F}_{ij} \approx \nabla^2 h\) generates a Bychkov-Rashba coupling of the form (Huertas-Hernando et al., 2006; Jeong et al., 2011; Ochoa et al., 2012a),

\[
\mathcal{H}_{BR} = g_{BR} \mathbf{F}_{ij} (\tau_z \sigma_x s_y - \sigma_y s_x).
\]

The tensorial nature of \(\mathcal{F}_{ij}\) allows for additional couplings, incorporating the effect of a preferential direction of bending (Ochoa et al., 2012a):

\[
\mathcal{H}'_{BR} = g_1 [(\mathcal{F}_{xx} - \mathcal{F}_{yy}) \tau_z s_y + 2\mathcal{F}_{xy} \tau_z s_x] + g_2 [(\mathcal{F}_{xx} - \mathcal{F}_{yy}) (\tau_z \sigma_x s_y + \sigma_y s_x) + 2\mathcal{F}_{xy} (\sigma_y s_y - \tau_z \sigma_x s_x)].
\]

From the previous tight-binding estimates we have (Jeong et al., 2011; Ochoa et al., 2012a)

\[
g_{BR} = \frac{a \epsilon \Delta_{SO}}{12V_{pp\sigma}^2} \approx 1.2 \text{ meV} \cdot \text{Å},
\]

\[
g_1 = \frac{aV_{pp\pi} \Delta_{SO}}{2(V_{pp\sigma} - V_{pp\pi})} \approx 1.5 \text{ meV} \cdot \text{Å}.
\]

where \(V_{pp\pi} \approx -2.2 \text{ eV}\) and \(V_{pp\sigma} \approx 5.4 \text{ eV}\) represent the hopping between \(p\)-orbitals at nearest neighbors. The second coupling in Eq. (7) only appears at second nearest neighbors, so it is usually neglected.

Since graphene is all surface, its environment sensitivity enables different ways of boosting its SOC including functionalization, adatom decoration and substrate engineering (Castro Neto and Guinea, 2009; Ferreira et al., 2013; Gmitra et al., 2013; Irmer et al., 2015; Ma et al., 2012; Pachoud et al., 2014; Soriano et al., 2015; Weeks et al., 2011). One of the first proposed strategies to enhance the SOC was the functionalization of graphene surface with hydrogen adatoms, which create a local out-of-plane, \(sp^3\)-like distortion of the surrounding bonds. This distortion hybridizes the \(\sigma\) states with the adjacent \(p\) orbitals, giving rise to an enhancement of the spin-orbit coupling (Castro Neto and Guinea, 2009),

\[
\Delta \approx \tan \vartheta \sqrt{1 - 2 \tan^2 \vartheta} \Delta_{SO},
\]

where \(\vartheta\) represents the angle of the distorted \(sp^3\)-bond with respect to the graphene plane (i.e., \(\vartheta = 0\) for the flat configuration). In the case of a complete \(sp^3\) hybridization \((\vartheta = 19.5^\circ)\) we have an enhanced SOC up to \(\Delta \approx 6 \text{ meV}\). The symmetry is effectively reduced down to \(C_{3v}\), so the specific couplings in the low-energy theory acquire different forms (Gmitra et al., 2013). Ab initio calculations give \(\Delta_{BR} \approx 0.33 \text{ meV}\) for the Bychkov-Rashba coupling. Notice that in this situation the bottleneck is still the weak intra-atomic spin-orbit interaction in carbon.

Balakrishnan et al. (2013) experimentally demonstrated a SOC enhancement of 2.5 meV in weakly hydrogenated graphene samples, see Fig. 6(a). Such enhancement caused the observation of spin Hall effect (SHE) at room temperature, with the spin-transport origin of the nonlocal signal confirmed by spin precession measurements. Similar results were also obtained in fluorinated graphene samples (Avsar et al., 2015). Nevertheless, other studies have reported large nonlocal signals in similarly hydrogenated devices but with an absence of
any magnetic field dependence in spin precession measurements (Kaverzin and van Wees, 2015), or contradicting the expectation of a decrease in spin lifetime due to larger SOC (Wojtaszek et al., 2013). These latest results suggest that the effect is sample dependent and there can be additional mechanisms involved other than spin transport, as theoretically suggested for the case of disorder in graphene (Van Tuan et al., 2016). These conflicting interpretations for experiments in hydrogenated graphene call for further studies to ensure a thorough verification of the role of SOC and the presence of the SHE in this system, and to further identify any other concomitant effect leading to the nonlocal response observed.

The passivation of $p_z$ orbital below the adatom creates a perfect vacancy (i.e., with no reconstruction altering the coordination of the lattice). Such a defect induces the formation of a quasi-localized state, manifested as a sharp resonance in the local density of states (Pereira et al., 2007; Wehling et al., 2010). The enhancement of the density of states at energies close to the Dirac point favors the formation of magnetic moments due to electron-electron interactions (Palacios et al., 2008; Yazey, 2008), which can modify both charge and spin transport properties. Non-perturbative calculations beyond mean field show no signature of saturation of the susceptibility at low temperatures (Haase et al., 2011), suggesting a ferromagnetic coupling between the quasi-localized magnetic moment and the itinerant spins. Nevertheless, experiments have so far demonstrated a paramagnetic response (McCreary et al., 2012; Nair et al., 2012).

Another direction to enhance the weak SOC of graphene is the decoration of its surface with heavy metallic adatoms (Brey, 2015; Ferreira et al., 2014; Hu et al., 2012; Ma et al., 2012; Pachoud et al., 2014; Weeks et al., 2011). In this approach, graphene’s $sp^2$ bond property is preserved; the SOC is locally enhanced due to tunneling of electrons from graphene to adatoms and back. Marchenko et al. (2012) observed a giant spin orbit splitting of $\approx 0.1$ eV in Au intercalated graphene samples. The photoelectron spectroscopy measurements revealed that hybridization with Au $5d$ states is the source of spin orbit splitting. Large spin orbit fields were also achieved in Pb intercalated graphene on Ir substrate (Calleja et al., 2015). Balakrishnan et al. (2014) demonstrated spin Hall effect at room temperature in CVD grown graphene devices, attributed to unavoidable residual Cu adatom clusters, with a SOC of $\approx 20$ meV. However, there are experimental controversies over nonlocal measurements in adatom decorated samples as well. For example, other groups also reported large nonlocal signals in Au and Ir decorated samples, but they did not observe any magnetic field dependence (Wang et al., 2015b). Further work is therefore needed to address the possible role of valley currents or of variations in adatom cluster sizes.

C. Transition-metal dichalcogenides and graphene

The family of atomically thin 2D crystals goes beyond the allotropes of carbon and already includes materials like phosphorene (Xia et al., 2014), graphene $C_2H_2$ (Elias et al., 2009), or monolayers of hexagonal boron nitride (hBN) (Watanabe et al., 2004), among others (Geim and Grigorieva, 2013). Silicene (A. Fleurence et al., 2012; Vogt et al., 2012), a single layer of silicon atoms forming a $sp^2$-like honeycomb lattice, has attracted much attention due to its resemblance with graphene. The spin-orbit coupling within the $\tau$ bands reduces to Eq. (5) as imposed by $D_{3d}$ point-group symmetry. Interestingly, the Kane-Mele coupling is much larger than in graphene, $\Delta_{KM} \sim 1.5$ meV, due to its buckled structure. For the same reason, the band topology can be controlled by applying a perpendicular electric field (Drummond et al., 2012; Ezawa, 2012).

The most appealing materials regarding spintronics applications are probably monolayers of transition-metal dichalcogenides (TMDC) (Wang et al., 2012). Bulk compounds are composed of X-M-X layers (X representing the chalcogen atoms, M the transition metal) stacked on top of each other and coupled by weak van der Waals forces. They show different polytypes which vary in stacking and atom coordination (Wang et al., 2012). Like graphite, these materials can be exfoliated down to a single layer (Gordon et al., 2002). Semiconducting materials include molybdenum disulfide (MoS$_2$), tungsten disulfide (WS$_2$), molybdenum diselenide (MoSe$_2$), or tungsten diselenide (WSe$_2$) (Mak et al., 2010).

The point group of the monolayer crystal is $D_{3h}$. The lattice consists in a triangular Bravais lattice with two X atoms and one M atom per unit cell. As in the case of graphene, the Fermi level lies around the two inequivalent corners of the hexagonal Brillouin zone. However, the dispersion and orbital character of the conduction and valence bands are completely different. The large crystal fields associated with the different atomic species prevent accidental degeneracies, so the bands remain gapped with approximately quadratic dispersion (Ordejón and Guinea, 2013; Rostami et al., 2013). The spin-orbit interaction splits the spin degeneracy of the bands,

$$H_{so}^{\text{tmd}} = \lambda_c \frac{1 + \sigma_z}{2} \tau_z s_z + \lambda_o \frac{1 - \sigma_z}{2} \tau_z s_z. \quad (10)$$

The magnitudes of the splittings in conduction and valence bands are very different due to their distinct orbital character, dominated by $d$ orbitals from the transition metal in both cases. A complete tight-binding model can be found in Roldan et al., 2014. Values extracted from $ab\text{ initio}$ calculations (Feng et al., 2012; Kormanyos et al., 2013; Zhu et al., 2011) are summarized in Table I. Notice that the splitting of the bands has opposite sign at each valley, as imposed by time-reversal symmetry. This spin-valley coupling (Xia et al., 2012) enables the
FIG. 6 Exploiting Spin-Orbit Coupling in Graphene. (a) Carrier concentration dependence of the nonlocal resistance in weakly hydrogenated and pristine graphene, shown as red and blue lines, respectively. The dotted gray line represents the calculated Ohmic contribution. The inset shows the dependence of the nonlocal resistance on the hydrogenation percentage. From Balakrishnan et al. (2013). (b) Back gate voltage ($V_{BG}$) dependence of the nonlocal resistance in graphene devices supported on WS$_2$. Spin precession and a sizeable signal are only detectable for $V_{BG} > 0$. From Avsar et al. (2014). (c) Magneto-transport measurements for graphene on WS$_2$ substrate, showing a weak anti-localization effect. From Wang et al. (2015c).

<table>
<thead>
<tr>
<th>Material</th>
<th>$\lambda$ (meV)</th>
</tr>
</thead>
<tbody>
<tr>
<td>MoS$_2$ (conduction band)</td>
<td>3</td>
</tr>
<tr>
<td>MoS$_2$ (valence band)</td>
<td>140</td>
</tr>
<tr>
<td>WS$_2$ (valence band)</td>
<td>430</td>
</tr>
<tr>
<td>MoSe$_2$ (valence band)</td>
<td>180</td>
</tr>
<tr>
<td>WSe$_2$ (valence band)</td>
<td>460</td>
</tr>
</tbody>
</table>

TABLE I Band spin splittings in monolayers of transition-metal dichalcogenides. Values from (Feng et al., 2012; Kormanyos et al., 2013; Zhu et al., 2011).

Compared to Eq. (2), two new terms appear in this Hamiltonian: the staggered potential $\Delta_{st}$, which opens a trivial gap in the spectrum, and the last term in the second line of Eq. (11), which removes the spin degeneracy of the bands. Both terms reflect that the symmetry of graphene is effectively reduced down to $C_{3v}$ due to the interaction with the underlying TMDC system. The model can be generalized to describe heterostructures with bilayer graphene, for which the induced spin-orbit coupling can be tuned by applying a perpendicular electric field (Gmitra and Fabian, 2017; Khoo et al., 2017).

Two distinctive band dispersions arise from this model, as represented in Fig. 7. In the first case (a) the staggered potential dominates over the induced spin-orbit coupling, whereas in the second (b) the spin-orbit coupling produces a band inversion. This second case is expected to occur for the heaviest atomic species in the second
layer (namely, W and Se). The band inversion resembles a time-reversal symmetric version of the quantum anomalous Hall effect proposed in graphene interacting with a heavy magnet (Qiao et al., 2014, 2010), where the term parametrized by λ can be interpreted as a valley-dependent exchange coupling. However, this band inversion does not correspond to a topological state, like in the idealized case of pristine graphene (Fig. 2): in general, two (instead of one) pairs of sub-gap helical modes connected by time-reversal symmetry appear at the boundaries of the system (Yang et al., 2016). Backscattering between states belonging to different Kramers doublets (in a zig-zag ribbon, one pair around the projected K and K’ points and the other at M) is only precluded by crystalline symmetries, which are removed by generic disorder. Moreover, the edges states are completely absent in armchair ribbons.

The approaches for enhancing SOC in graphene previously discussed in Section II.B, regarding functionalization (Avsar et al., 2015; Balakrishnan et al., 2013) and adatom decoration (Balakrishnan et al., 2014), had the downside of reducing the electronic quality of graphene. On the other hand, creating a van der Waals interface between graphene and a TMDC can enhance the SOC of the former while simultaneously preserving its high electronic mobility (Tan et al., 2014). Towards this, Avsar et al. (2014) demonstrated a three orders of magnitude enhancement of SOC strength by bringing graphene into proximity with WS$_2$. The resulting large SOC strength of up to 17.6 meV led to the observation of (1)SHE for transport in the electron regime, attributed to sulfur-based in-gap defect states, see Fig. 6(b). The large spin orbit coupling in sulfur vacancies in monolayer WS$_2$ has been recently confirmed by detailed scanning probe microscopy studies (Schüler et al., 2018).

The relative strength of the induced spin-orbit couplings can be extracted from magneto-transport experiments. Wang et al. (2015c) demonstrated pure interface-induced SOC enhancement by performing weak anti-localization measurements, see Fig. 6(c). The last two terms in Eq. (11) possesses different symmetry with respect to mirror reflection, which provides different signatures in the quantum-interference correction to the conductivity. In the absence of inter-valley scattering, the magneto-conductance is given by (McCann and Fal’ko, 2012)

$$
\Delta G = -\frac{e^2}{2\pi\hbar} \left[ F \left( \frac{B}{B_0} \right) - F \left( \frac{B}{B_\phi + 2B_{asy}} \right) \right] - 2F \left( \frac{B}{B_\phi + B_{sym} + B_{asy}} \right),
$$

where $F(z) = \log z + \Psi(1/2 + 1/z)$, $\Psi(x)$ is the digamma function, and $B_i \equiv h/(4\ell_{i}^2)$. Here $\ell_{sym(asy)}$ correspond to the spin diffusion lengths limited by mirror symmetric (asymmetric) spin-orbit terms, whereas $\ell_{\phi}$ represents the phase-coherence length limited by inelastic scattering (phonons or electron-electron interactions). While spin dephasing induced by mirror asymmetric terms (i.e., the Bychkov-Rashba coupling) should be manifested as a weak anti-localization effect at low temperatures and fields, the mirror symmetric terms (i.e., the spin-valley locking term $\lambda$) introduces an effective saturation of the decoherence times, leading to a suppression of the magneto-conductance at the lowest fields ($B < B_{sym}$). A similar crossover is expected in TMDC monolayers (Ochoa et al., 2014). In hybrid graphene-TMDC systems, a weak anti-localization behavior is systematically reported, as discussed previously, in a wide range of carrier concentrations (Wang et al., 2015c, 2016; Yang et al., 2017, 2016), suggesting a dominance of mirror asymmetric terms. Extracting the strength of the couplings requires the knowledge of the underlying spin-relaxation mechanism, which is the subject of Section III.A. Overall, the observation of similar results with different dichalcogenides indicates the robust and strong nature of proximity-induced SOC enhancement in graphene-TMDC heterostructures.

### D. Graphene/TMDC optospintronics

Non-destructive optical spin injection into graphene has the potential to overcome limitations inherent to electrical spin injection methods whilst enabling new optospintronic functionalities. The weak optical absorption and weak intrinsic SOC strength of graphene prevents such a direct optical spin injection. In this regard, Gmitra and Fabian (2015) proposed the use of proximity-induced SOC as way to enable direct optical spin injection. Here, graphene is partially covered by a monolayer transition-metal dichalcogenide crystal, as shown in Fig. 8(a). Excitation with circularly polarized light on the TMDC-covered graphene area generates spin polarized charge carriers in the TMDC monolayer, as a result of spin-valley coupling and the valley-selective absorption. These carriers diffuse into the adjacent graphene layer, and are finally detected electrically using ferromagnetic contacts in a non-local geometry. This non-destructive optical spin injection schemes were recently experimentally realized independently by two groups. Luo et al. (2017) utilized monolayer MoS$_2$ to inject spin current into multilayer graphene at room temperature. They utilized Hanle spin precession measurements to confirm optical spin injection, spin transport and electrical detection, see Fig. 8(b). Avsar et al. (2017b), utilized monolayer WSe$_2$ to inject spin current into monolayer graphene, where the generated nonlocal spin signal was electrically detected by utilizing hBN as a tunnel barrier. The spin-coupled valley selective origin of the signal was confirmed by prudentely studying the dependences of the nonlocal spin signal on modulations of the incident
FIG. 8 Alternative Spintronics in Graphene and Other 2D Materials. (a) Schematics of optical spin injection in graphene (gray) by utilizing a monolayer transition metal dichalcogenide (green) and excitation with circularly polarized light. From Gmitra and Fabian (2015). (b) Hanle spin precession curves for different detector magnetization directions in a graphene/MoS\textsubscript{2} device. From Luo et al. (2017). (c) Incident angle dependence of optically generated nonlocal signal under quarter wave modulation in a graphene/WSe\textsubscript{2} device. From Avsar et al. (2017b).

light intensity and polarization, see Fig. 8(c). In future experiments it will be relevant to determine the types of charge carriers diffusing into graphene, as well as experimentally demonstrating the optical detection of such generated spin signal, free from any contact-related spin scattering at FM/NM interfaces.

III. CURRENT CHALLENGES AND WAY FORWARD

A. What is the dominant spin relaxation mechanism?

The polarization of a spin current in a metal or semiconductor device decays during the propagation of the spin carriers. Defining a characteristic time of decay in a rigorous way is a difficult task, though. This is usually introduced within the framework of the Bloch-Torrey equations (Bloch, 1946; Torrey, 1956) describing the macroscopic dynamics of the spin density in the material. Related phenomenological models can be used to fit the experimental data and extract characteristic times of spin relaxation. However, a theoretical evaluation requires more sophisticated models for the microscopic spin dynamics. Once this is determined, a quantum kinetic equation for the spin-ensemble dynamics can be derived (Mishchenko et al., 2004). Microscopic expressions for the relaxation rates can be obtained in the limit of long wave-lengths, in which the variations of the density matrix are smooth on the scale of the characteristic length of the problem, e.g., the mean-free path $\ell$ in the diffusive regime (Burkov et al., 2004). This procedure is usually simplified by a semi-classical treatment based on the spin-Boltzmann equation. This approach has been applied to the study of spin relaxation in single-layer (Dugaev et al., 2011; Zhang and Wu, 2011, 2012a; Zhou and Wu, 2010) and bilayer (Diez and Burkard, 2012) graphene, and more recently in transition-metal dichalcogenides (Wang and Wu, 2014a,b).

Four main mechanisms of spin relaxation are usually discussed for metals and semiconductors (Žutić et al., 2004): the Elliot-Yafet (Elliot, 1954; Yafet, 1963), D’yakonov-Perel’ (D’yakonov, 2008; D’yakonov and Perel’, 1971), Bir-Aronov-Pikus (Bir et al., 1975), and hyperfine-interaction mechanisms (D’yakonov and Perel’, 1973). The last two are usually disregarded in the context of graphene. On the one hand, the natural abundance of carbon isotopes with nuclear magnetic moment is very low; also, the nuclear fields acting on the spin of itinerant electrons averages-out in the diffusive limit, so this contribution can be safely neglected in the experimental situations that we are going to discuss here (Wojtaszek et al., 2014). On the other hand, the Bir-Aronov-Pikus mechanism accounts for electron spin-flip processes mediated by the electron-hole exchange interaction, and therefore it is only relevant in heavily $p$-doped semiconductors.

The Elliot-Yafet (EY) mechanism takes into account the change in the spin polarization of a Bloch electron due to scattering off phonons or impurities. It is characterized by a linear relation between the spin and the quasimomentum relaxation times, $\tau_s = \alpha \tau_p$, where $\alpha$ can be interpreted as the spin-flip probability during a scattering event. This relation can be deduced by treating the spin-orbit interaction perturbatively and holds experimentally for most conventional metals (i.e., systems with well-defined Fermi surface). In doped graphene, the EY mechanism is dominated by inter-band transitions and the EY relation depends explicitly on the carrier concentration (Huertas-Hernando et al., 2009; Ochoa et al.,
Here $\Delta$ represents the strength of the spin-orbit interaction within the $\pi$-bands and $\epsilon_F = h\nu_F\sqrt{\pi n}$ is the Fermi energy with respect to the Dirac point, where $n$ represents the carrier concentration. For typical values of these parameters, $\Delta \approx 10$ $\mu$eV, $n = 10^{12}$ $cm^{-2}$, and $\tau_p = 10$ fs, the spin relaxation times due to the EY mechanism are of the order of $\tau_s \approx 10$ $\mu$s, $\approx$ 4 orders of magnitude longer than the relaxation times reported in Hanle precession experiments.

The Dyakonov-Perel’ (DP) mechanism accounts for the spin dephasing in between scattering events. As we discussed earlier, the doubly degeneracy of the bands is lifted in non-centrosymmetric crystals, and the spin-orbit coupling can be interpreted as an effective Zeeman field that makes the electron spin to precess in the Bloch sphere. The axis of precession depends on the direction of motion of the electron, and therefore scattering randomizes the process. This is an example of motional narrowing, characterized by inverse relation between the spin and the quasi-momentum relaxation times (Fabian et al., 2007),

$$\frac{1}{\tau_s} \approx \left(\frac{\Delta_{BR}}{\hbar}\right)^2 \tau_p^{-1}. \tag{13}$$

The term in parentheses must be interpreted as the effective Larmor frequency associated with a Bychkov-Rashba coupling generated by, e.g. the interaction with the substrate (Ertler et al., 2009). Realistic estimates lead to $\tau_s \approx 1$ $\mu$s, again much longer than the relaxation times reported in Hanle precession. This discrepancy in several orders of magnitude along with the shortcomings of Eqs. (13)-(14) to reproduce the intricate behavior of $\tau_s$ as a function of doping or temperature (particularly in the case of bilayer graphene) has provoked a tremendous activity in the recent years.

1. Intrinsic relaxation sources

As we discussed earlier, out-of-plane displacements enhance the strength of the spin-orbit coupling within the $\pi$-bands due to hybridizations with higher $\sigma$-states. Therefore, flexural phonons (the quanta of these vibrations) represent an unavoidable source of spin decoherence in clean, free-standing graphene. In fact, flexural phonons constitute the leading scattering mechanism in suspended samples at temperatures $T \gtrsim 10$ K, limiting the electron mobilities down to few $m^2/Vs$ (Castro et al., 2010). Their contribution to spin relaxation can be evaluated from the couplings in Eqs. (6)-(7), leading to (Fratini et al., 2013; Vicent et al., 2017)

$$\frac{1}{\tau_s} = \frac{\bar{g}^2 k_F}{2\hbar^2 v_F} \frac{k_B T}{\kappa} \left(\frac{2k_F}{q_c}\right)^{2\nu}, \tag{15}$$

where $\bar{g}^2 \equiv g_{BR}^2 + g_0^2/4 + g_0^2$ is the effective spin-phonon coupling. Here $\nu = 0, 1$ corresponds to the free-standing regime ($q_c \ll 2k_F$, where $k_F$ is the Fermi momentum of carriers and $q_c$ represents an infrared cut-off of the harmonic phonon dispersion) and samples under tension, respectively. In the former case, the dispersion relation of flexural phonons is approximately quadratic, $\omega_q = \sqrt{\kappa/\rho} |q|^2$, where $\kappa \approx 1$ eV (Kudin et al., 2001) is the bending rigidity. At momenta $|q| < q_c$, the dispersion relation is effectively linearized due to anharmonic effects (Zakarchenko et al., 2010) or applied tensions, altering the dependence on the Fermi wavevector $k_F = \sqrt{\pi n}$ when the strain exceeds $\bar{u} \approx 4\pi n\nu/K$, $K \approx 21$ eVÅ$^{-2}$ being the two-dimensional bulk modulus (Lee et al., 2008). In free-standing graphene, the spin relaxation times are of the order of hundreds of nanoseconds at room temperature, rapidly decreasing when tension is applied. Note also that the spin-relaxation rate in Eq. (15) grows linearly with the temperature, in contrast to momentum scattering, dominated by two-phonon processes. This leads to a distinctive $T^2$-dependence in the mobilities of suspended samples (Castro et al., 2010), so the spin-relaxation times are expected to deviate from Eq. (13) in the clean limit.

In supported samples, graphene remains pinned to the substrate and the contribution from flexural phonons is strongly suppressed. Nevertheless, the interaction with the substrate enhances the spin-orbit coupling and induces spin relaxation (Ertler et al., 2009). On top of that, supported graphene sheets also present static corrugations with characteristic heights of $\sim 0.3$ nm (Locatelli et al., 2010), which in the simplest approximation creates a non-uniform Bychkov-Rashba coupling. In the diffusive limit, we end up with two different regimes of spin relaxation arising from the competition between the two relevant length scales in the problem, the mean free path, $\ell$, and the lateral size of the ripples, $\mathcal{L}$. In the scattering-dominated regime, $\ell \ll \mathcal{L}$, spin decoherence is limited by the conventional motional narrowing. In between scattering events, the electron spin precesses an angle $\delta$, which can be estimated from the Larmor frequency $\Delta_{BR}/\hbar$, where $\Delta_{BR} \approx 9g_{BR} \times h/\mathcal{L}^2$ is the average strength of the corrugation-induced spin-orbit coupling. After $N$ collisions, and assuming that the process is Markovian, the precession angle is about $\delta(N) \sim \Delta_{BR}/\hbar \times \tau_p \times \sqrt{N}$. The spin-relaxation time may be defined as the time after which the precession angle is $\delta(N_s = \tau_s/\tau_p) \sim 1$, from which we deduce the DP relation in Eq. (14). On the contrary, if $\ell \gg \mathcal{L}$ the randomization process is dominated by the spatial fluctuations in the strength of the spin-orbit coupling (Dugaev
et al., 2011). Within a region of characteristic size $L$ we have $\delta \sim \mathcal{L} \Delta_{BR}/(\hbar v_F)$, and then after a time $t$ we end up with $\delta(t) \sim \sqrt{\mathcal{L} \mathcal{F}} \times \Delta_{BR}/\hbar$. From the previous arguments we obtain $\tau_s \sim (\Delta_{BR}/b)^2 \times \mathcal{L}/\sqrt{\mathcal{F}}$ in that case. Typical ripples in graphene extend over $L \approx 10-50$ nm ($\ll \ell$), so we expect the spin-relaxation times to be determined by geometrical parameters only and not by the scattering times. Diffusion-barrier-induced corrugations in epitaxial growth fronts are also characterized by a constant periodicity, systematically observed in chemical-vapor deposited (CVD) samples. Experimentally, however, corrugations do not seem to play an important role in spin transport (Avsar et al., 2011), manifesting basically the same features in CVD graphene as in exfoliated samples.

So far, neither of these mechanisms rely on the characteristic Dirac spectrum of low-energy graphene quasiparticles. Numerical studies suggest that the entangled dynamics of the spin and pseudo-spin degrees of freedom (the latter associated with the projection of the wave function onto the Fermi surface) leads to fast spin relaxation at energies close to the Dirac point (Tuan et al., 2014). This mechanism qualitatively explains the dependence of $\tau_s$ on the carrier concentrations, which cannot be attributed to the usual EY and DP relations, Eqs. (13) and (14). Experimental validation of the roles of spin and pseudospin degrees of freedom (Roche and Valenzuela, 2014) and of their relative contributions compared to other sources (e.g. extrinsic, see next section) is crucial to understand the nature of spin relaxation, which is one of the fundamental long-standing puzzles in the way to the full maturity of the field of graphene spintronics.

2. Extrinsic sources: impurities

The observed small spin relaxation times in graphene could have an extrinsic origin. Kochan et al. (2014) proposed that local magnetic moments localised on resonant impurities behave as spin hot spots and cause high spin relaxation rates. Based on this mechanism, electrons tend to stay around the impurity (Huang et al., 2016) and spins flip is due to the exchange interaction with the magnetic moment on the impurity. Quantitative agreement with experiment on spin relaxation times was achieved even for very low concentration of local moments. It was also predicted that spin relaxation times in single and bilayer graphene have opposite dependences on carrier concentration (Kochan et al., 2015). This opposite dependence was experimentally verified by carrier concentration dependent spin transport measurements in hBN encapsulated graphene (Avsar et al., 2016). The latter work also probed a sharp increase of spin relaxation time in bilayer graphene at high carrier densities, which similarly could be explained with the resonant scattering theory. The source of resonant magnetic scatterers is hypothesized to be polymer residues from the device fabrication.

Moreover, Eq. (13) is not consistent with the approximately linear scaling between $\tau_s$ and the diffusion constant at different gate voltages observed in many experiments (Avsar et al., 2011; Han and Kawakami, 2011; Józsa et al., 2009a; Yang et al., 2011). The experiments by Jo et al. (2011) are a notable exception for which the relation in Eq. (13) seems to hold. The large spin-orbit coupling required to fit the data ($\Delta \approx 10$ meV, close to the intra-atomic coupling in carbon) suggests that covalently attached adatoms instead of charged impurities dominate spin transport in that case. A unifying theory is provided by Zhang and Wu (2012b), suggesting that both the EY and D'yakonov-Perel' mechanisms cohabit in general, their relative strength being dictated by ambient conditions.

B. Advances in spin injection contacts

A tunnel barrier is a key element of graphene spin valve devices to alleviate the conductivity mismatch problem, which dictates that the spin injection efficiency decreases if the contact resistance is too low (Rashba, 2000). To achieve a spin dependent tunnel barrier, the pioneering work of Tombros et al. (2007) utilized an electron beam evaporator to grow $\approx 0.6$ nm thick Al layer on graphene under high vacuum conditions, followed by its oxidation in a 100 mbar O$_2$ pressure. These initial devices and the follow up works using MgO barriers typically exhibit spin injection efficiencies of $\approx 5\%$ (Wang et al., 2008; Yang et al., 2011). On the other hand, Dlubak et al. (2012a, 2010), characterized sputter deposited Al$_2$O$_3$ and MgO layers. Sputter deposition is a standard method to grow barriers in tunnel magnetoresistance (TMR) structures, and resulted in nearly pinhole free $\approx 1$ nm thick Al$_2$O$_3$ barrier on graphene. Nevertheless, this method destroyed the structural quality of graphene sheets, as evidenced by the observation of strong Raman peaks associated with defects (Dlubak et al., 2012a). Spin valves prepared with Al$_2$O$_3$ barriers grown by atomic layer deposition similarly achieved spin injection efficiencies of $\approx 5\%$ (Yamaguchi et al., 2012). Furthermore, Komatsu et al. (2014) oxidized thermally evaporated yttrium barriers in air, to form $1$ nm thick yttrium-oxide tunnel barriers and achieving spin injection efficiency of $15\%$.

Although most spin injection barriers dominated by pinholes, e.g. using MgO or Al$_2$O$_3$, allowed spin injection and detection, the extracted short spin relaxation lengths were associated with contact induced spin scattering. Therefore a significant effort has been given to improve the quality of these barriers. In this regard, Han et al. (2010) achieved tunnel spin contacts with polarization up to 30%, by adding a thin Ti seed layer at the interface of MgO and graphene. Spin signals up to
150 130 Ω were observed, two orders of magnitude higher than the typical values achieved by using transparent contacts, see Fig. 9(a). Consequently, these devices exhibited improved spin relaxation times of up to 0.5 ns. Furthermore, Drögeler et al. (2016) increased spin relaxation times up to 12 ns by utilizing MgO barriers evaporated on Cobalt electrodes, just before the mechanical transfer of a encapsulating graphene/hBN heterostructure. Curiously, contact resistance measurements and scanning force microscopy show the presence of pin-holes in the MgO barrier, Fig. 9(b).

2D crystals such as functionalized graphene or hBN are expected to act as ideal ultrathin tunnel barriers, without pinholes. Prior to spin transport measurements, the potential of hBN as a tunnel barrier was demonstrated by Britnell et al. (2012). Their results showed that hBN layers fulfill all requirements for a most favorable tunnel barrier (Jönsson-Akerman et al., 2000): 1) It has non-linear but symmetric I-V dependence, 2) such dependence is weakly sensitive to temperature, 3) the resistance of the barrier depends exponentially on thickness, see Fig. 9(c), and 4) it is pin-hole free. Reported spin valve devices so far have utilized monolayers of exfoliated or CVD-grown hBN, which have comparable resistance with the graphene channel itself (Fu et al., 2014; Gurram et al., 2016; Kamalakar et al., 2014; Yamaguchi et al., 2013). Therefore most of these devices are within the conductivity mismatch range and do not take full advantage of hBN as a tunnel barrier. As a different approach, Friedman et al. (2014, 2015) used chemically functionalized graphene as a tunnel barrier. From the nonlocal spin valve measurements, they achieved spin injection efficiencies up to 45% and 17% at low temperatures for fluorinated and hydrogenated graphene-based tunnel barriers, respectively. However calculated spin relaxation times in these devices are less than 0.2 ns and the created spin accumulation is very small or even absent at room temperature (Friedman et al., 2016). Recently, Gurram et al. (2017) have observed bias-induced enhanced spin injection and detection efficiencies up to 100% in tunnel junctions with bilayer hBN barriers. Similar results were obtained for trilayer hBN tunnel barriers (Leutenantsmeyer et al., 2018b). These results are not yet understood.

C. Alternative spin injection and detection techniques

Besides the use of electrical and optical means, ferromagnetic resonance spin pumping has also been utilized to inject spins into graphene. In this technique, a ferromagnet is placed in contact with graphene and the magnetization of the ferromagnet is driven into resonant precession by the use of an oscillating magnetic field. The angular momentum transfer from the precessing ferromagnet drives a spin current into graphene, while this spin transfer is observed as an enhanced damping of the ferromagnetic resonance. Different than the electrical spin injection method, this dynamical method does not require any tunnel barrier as it allows injection via transparent interfaces. (Patra et al., 2012) reported the first evidence of spin pumping into chemically grown graphene by demonstrating a remarkable broadening of the ferromagnetic resonance absorption peak in Py/graphene and Co/graphene films. The significant absorption of angular momentum suggested that SOC strength in proximitized CVD graphene is larger than for pristine graphene (Patra et al., 2012; Singh et al., 2014).
FIG. 10  *Electric-Field Dependent Spin Transport in 2D-based Heterostructures.* (a) The amplitude of the detected spin signal as a function of drift current, demonstrating spin drift. Inset shows the measurement geometry. From Ingla-Aynés *et al.* (2016). (b) Dependence of nonlocal spin signal in bilayer graphene on the local resistance at the Dirac point. The latter increases with the vertical electric field (from yellow to purple dot). At higher fields, the spin current is switched off by the gapped channel. Top inset shows spin valve measurements at zero (dark yellow line) and high (black line) displacement fields, demonstrating a spin switch effect. From Aysar *et al.* (2016). (c) Oblique Hanle measurements near the charge neutrality point in a bilayer graphene spin valve, for different angle $\beta$ relative to the graphene plane. The magenta curve is a fit to the experimental data (blue points) and reveals an anisotropy of $\sim 12$ in the spin relaxation time. Away from the charge neutrality point, the anisotropy diminishes and the response becomes similar to the cyan dashed line. From Xu *et al.* (2018).

Still, the exclusive use of ferromagnetic broadening to quantify spin injection was cautioned by the work of Berger *et al.* (2014), which demonstrated that cobalt grown on graphene has enhanced magnetic disorder and hence the observed broadening may have a contribution from the structural change of the ferromagnet. This uncertainty was addressed by the work of Tang *et al.* (2013), which unambiguously proved dynamical spin injection at room temperature by detecting the injected spin current via the inverse SHE (ISHE) in Pd electrodes. A similar approach was later shown using the ISHE of graphene itself (Ohshima *et al.*, 2014). Similar to ISHE, there are other methods for electrically probing spin transport in graphene. Detailed quantum interference measurements, combining weak localization and universal conductance fluctuations, probed decoherence in graphene (Lundeborg *et al.*, 2013) and indicated that magnetic defects are the dominating source of spin scattering. This identification of an extrinsic source of spin relaxation in the form of magnetic defects is in agreement with later theoretical predictions (Kochan *et al.*, 2015) and spin valve measurements (Aysar *et al.*, 2016).

The unique electronic structure of graphene paves the way for unconventional ways to detect and create spin transport, even without using magnetic contacts. Under a large applied magnetic field, graphene devices in a Hall bar geometry exhibit a giant nonlocal resistance (Abanin *et al.*, 2011b). This phenomenology, similar to that of the SHE, was attributed to the creation of spin-up electrons and spin-down holes due to Zeeman splitting near the charge neutrality point, without any role of SOC (Abanin *et al.*, 2011a). A further work indicated that thermoelectric effects, i.e., the interaction between thermal and electronic transport, could have a contribution to this nonlocal signal as well (Renard *et al.*, 2014). The insight that thermoelectric transport is interrelated with spin transport has developed in recent years into the active subfield of spin caloritronics (Bauer *et al.*, 2012). This interrelation was demonstrated in graphene via the detection of spin currents without the use of magnetic contacts (Vera-Marun *et al.*, 2012), where the spin-to-charge conversion mechanism relies on the energy-dependent transmission of graphene itself (Ohashima *et al.*, 2014). Similar to ISHE, there are other methods for electrically probing spin transport in graphene. Detailed quantum interference measurements, combining weak localization and universal conductance fluctuations, probed decoherence in graphene (Lundeborg *et al.*, 2013) and indicated that magnetic defects are the dominating source of spin scattering. This identification of an extrinsic source of spin relaxation in the form of magnetic defects is in agreement with later theoretical predictions (Kochan *et al.*, 2015) and spin valve measurements (Aysar *et al.*, 2016).

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**D. Vertical junctions for spin memories**

Several 2D crystals, including graphene, hBN and MoS$_2$, have been integrated into vertical GMR and TMR structures as non-magnetic barriers (Chen *et al.*, 2013; Cobas *et al.*, 2013, 2012; Dankert *et al.*, 2014a; Godel *et al.*, 2014; Iqbal *et al.*, 2013; Li *et al.*, 2014; Meng *et al.*, 2013; Wang *et al.*, 2015a). These structures are the most
prominent class of spintronic devices, widely used as magnetic sensors. Other uses include graphene as a barrier for spin injection into semiconductors (Erve et al., 2012), to prevent oxidation of ferromagnetic electrodes (Dhlubak et al., 2012b), or as a spin-conserving channel in a hot-electron transistor (Banerjee et al., 2010).

Interest towards the integration of 2D crystals in vertical structures was driven by the prediction that few-layer graphene could act as a perfect spin filter (Karpan et al., 2007, 2008; Yazyev and Pasquarello, 2009). Improved advancements on device fabrication have allowed to study the nature of magnetoresistance in graphene and hBN based vertical devices, evidencing the role of charge transfer and proximity effects. The latter include the spin-splitting induced in graphene due to proximity to the ferromagnetic electrodes (Asshoff et al., 2017), and to identify the role of individual resonant defect states in hBN to enhance TMR (Asshoff et al., 2018). All these approaches set the prospect of engineering vertical magnetoresistance in 2D-based junctions, which are the key elements within current memory architectures of magnetic random access memories (Parkin et al., 2003).

E. Electric-field effect in mono- and bilayer-graphene

As discussed previously, hBN has also been employed to develop device concepts which could pave the realization of new types of spin-based logic transistors. In a dual-gated device architecture utilizing hBN as a dielectric layer, Ingla-Aynés et al. (2016) controlled the propagation of spin current at room temperature using the drift of electron spins, as shown in Fig. 10(a). Here, the spin relaxation length of 7.7 μm, was demonstrated to be controlled from 0.6 μm up to 90 μm when a DC current of ±90 μA was applied. Depending on the polarity of the DC current, directional control of spin transport was achieved. This spin drift effect demonstrated how longitudinal electric fields can guide and extend the propagation of spin current.

A similar dual-gated structure, this time using bilayer graphene, was also employed to study a different phenomenon: the role of perpendicular electric fields. Here a transport gap was induced on bilayer graphene by the application of a vertical electric field at low temperature, which allowed a purely electrostatic control of spin current propagation (Avsar et al., 2016). In an entirely opposite trend to the device resistance, the spin signal near the charge neutrality point was observed to rapidly decrease as the displacement field was increased, and eventually the signal becomes undetectable. This device therefore served as an spin-transport analogy to the charge-based field-effect transistor, demonstrating a full electrostatic-gate control of spin current propagation, see Fig. 10(b). Furthermore, the unique spin-valley coupled band structure of bilayer graphene in such dual-gated device architecture enables the exciting possibility of modulating the spin-lifetime anisotropy. By performing Hanle spin precession measurements under obliquely oriented magnetic fields, Xu et al. (2018) demonstrated that the ratio between out-of-plane (7.8 ns) and in-plane (0.64 ns) spin lifetimes is as large as ~ 12 near the charge neutrality point, as shown in Fig. 8(c). Such a large anisotropy is a result of an out-of-plane spin orbit field originated from the induced-band gap in bilayer graphene. When increasing the carrier concentration under a fixed vertical displacement field, both in-plane and out-of-plane spin lifetimes eventually become comparable and therefore the anisotropy disappears. These groundbreaking results, which offer a novel approach to manipulating spin information, were independently demonstrated by Leutenantsmeyer et al. (2018a) as well.

F. Proximity-enabled graphene/TMDC novel devices

The ability to control both the flow of spin information and the anisotropy of spin lifetime via an electrostatic gate in bilayer graphene relies on the presence of its band gap, which is only evident in experiments at low temperature. On the other hand, similar electrostatic control of spin information has been recently realized at room temperature, by exploring graphene/TMDC heterostructures. Electric field-controlled spin current in graphene/MoS₂ spin valve devices was first reported as a result of gate-tunable spin absorption into the adjacent MoS₂ layer (Dankert and Dash, 2017; Yan et al., 2016), see Fig. 9(a). Later, two independent groups demonstrated that strong spin-valley coupling in WS₂ or MoS₂ results in a change of over one order of magnitude between the spin lifetimes for in-plane and out-of-plane spins (Benítez et al., 2018; Ghiasi et al., 2017), see Fig. 9(b-c), in good agreement with earlier theoretical predictions (Cummings et al., 2017). These encouraging results in heterostructure systems enabled further theoretical investigations focusing on converting charge current into spin current, either using the Spin Hall effect (SHE) which can be induced via proximity in graphene (Garcia et al., 2017; Milletari et al., 2017) or the Rashba-Edelstein effect (RRE) present at the graphene/TMDC interface (Offidani et al., 2017). The corresponding inverse effects (ISHE and IRRE) are also possible, leading to reciprocal spin to charge conversion. Towards this direction, Safeer et al. (2019) studied graphene/MoS₂ heterostructures and demonstrated the presence of a proximity-induced ISHE in graphene, with an additional spin to charge conversion mechanism that could be indistinguishably attributed to either a proximity-induced IRRE in graphene or ISHE within the MoS₂ layer (Fig. 9(d)). Soon after, charge-to-spin conversion due to RRE in a graphene/monolayer WS₂ heterostructure was demonstrated, also evidencing its car-
FIG. 11  Proximity-enabled graphene/TMDC devices. (a) Nonlocal spin signal and conductivity for graphene/MoS$_2$ device, demonstrating a field-controlled spin absorption. From Yan et al. (2016). (b) Top schematic shows the spin precession cone under an oblique magnetic field, applied in a plane that contains the easy axis of the ferromagnetic electrodes and that is perpendicular to the substrate. Bottom schematic shows the spin precession with magnetic field applied in plane and perpendicular to the easy axis of ferromagnets. Here, the spin precesses on a plane perpendicular to the substrate. From Benítez et al. (2018). (c) Anisotropy measurements in a graphene/WS$_2$ spin valve device. Solid green dots represent the measurements taken at $V_{BG} = -15$V, with the green line a fit revealing an anisotropy of $\sim 10$. Open black dot shows data acquired in a reference graphene spin valve without WS$_2$, lacking any anisotropy. From Benítez et al. (2018). (d) Spin-to-charge conversion in a Hall bar detector within a graphene/MoS$_2$ heterostructure, at different temperatures. The inset shows the measurement configuration. From Safeer et al. (2019).

FIG. 12  Spintronics in 2D Materials Beyond Graphene. (a) Spin transport in black phosphorus spin valves. Top panels show the device schematics and the optical image of a completed device, respectively. Bottom panels show spin valve and spin precession curves taken at 100 K, respectively. From Avsar et al. (2017a). (b) Polar magneto-optical measurement for CrI$_3$, showing hysteresis for ferromagnetic monolayer (1L) and trilayer (3L), and vanishing Kerr rotation for antiferromagnetic bilayer (2L). From Huang et al. (2017). (c) Upper panel represents the device geometry, where electrolyte gating technique was employed to induce an electric field. This tunes the density of states in magnetic Fe$_3$GeTe$_2$. Bottom panel shows the anomalous hall effect measurements as a function of temperature in a four-layers-thick Fe$_3$GeTe$_2$. From (Deng et al., 2018)

rier density and temperature dependences (Ghiasi et al., 2019). Similarly, REE at room temperature was also observed in a graphene/TaS$_2$ heterostructure (Li et al., 2019). These recent experiments unambiguously prove charge-to-spin conversion via proximity-induced effects (SHE, RRE), by combining Hall probes with standard ferromagnetic electrodes within the same device architecture. The latter is a critical advancement compared to the earlier proximity studies, which utilized only Hall bar (non-magnetic) electrodes (Avsar et al., 2014; Wang et al., 2015d).
G. Spintronics with 2D semiconductors and 2D magnets

Spintronics in 2D semiconductor materials such as black phosphorus (BP) and TMDCs can offer functionality that is not possible by using only graphene, for example gate controlled amplification/switching actions. Towards this, Aysar et al. (2017a) demonstrated all electrical spin injection, transport, manipulation and detection in ultrathin BP-based spin valves at room temperature. Based on four-terminal Hanle spin precession measurements, spin relaxation times up to 4.5 ns with spin relaxation lengths exceeding 6 μm were extracted, see Fig. 12(a).

Temperature and gate voltage dependences for spin and momentum relaxation times were in good agreement with first-principles calculations, showing that Elliott-Yafet relaxation is dominant in BP (Kurpas et al., 2016; Li and Appelbaum, 2014). Further work is required to explore other spintronic properties, like directional spin transport in this anisotropic crystal.

Initial efforts to investigate magnetism in 2D materials mostly focused on proximity induced (Wang et al., 2015d) and defect induced (Yazyev and Helm, 2007) magnetism. Based on the Mermin-Wagner theorem (Mermin and Wagner, 1966), intrinsic ferromagnetic order is indeed not expected in 2D single layers. This was initially supported by the experimental results obtained from 2D Cr$_2$Ge$_2$Te$_6$ where magnetism is absent in its monolayer, at least down to the lowest studied temperatures (4.7 K) (Gong et al., 2017). In this material ferromagnetic order persists nonetheless down to bilayer, but the critical temperature significantly decreases from 68 K (bulk) to 30 K (bilayer), which can be explained by the thermal excitation of spin waves.

On the other hand, the Mermin-Wagner restriction can be lifted if a material displays strong SOC and magnetocrystalline anisotropy. As shown in Fig. 12(b), layer dependent magnetic ordering in CrI$_3$ was demonstrated down to monolayer thickness, with its spins constrained to lie vertical to the lattice plane as described by the Ising model (Huang et al., 2017). The layered structure of CrI$_3$ provides interesting opportunities: an odd number of layers results in long range ferromagnetic ordering, while an even number are antiferromagnetic. In the bilayer case, application of an external magnetic field above the coercive field makes the material ferromagnetic; all layers are aligned to the same directions. By taking advantage of this polarization switch, giant tunneling magnetoresistance was demonstrated in vertically studied samples (Klein et al., 2018; Song et al., 2018; Wang et al., 2018). At constant voltage bias, such a magnetoresistance changes the current by nearly one million percent if thicker CrI$_3$ is employed (Kim et al., 2018). It was also demonstrated that the critical field required to switch from antiferromagnetism to ferromagnetism depends on the vertically applied electric field, see Fig. 12(c) (Huang et al., 2018; Jiang et al., 2018).

Demonstration of 2D magnetism in Cr$_2$Ge$_2$Te$_6$ and CrI$_3$ has pushed a rapid progress towards the discovery of new 2D magnetic materials, such as CrBr$_3$ (Ghazaryan et al., 2018), Fe$_3$GeTe$_2$ (Deng et al., 2018) and VSe$_2$ (Bonilla et al., 2018). Based on magneto-optical measurements, it was shown that VSe$_2$ shows ferromagnetic ordering persisting up to room temperature in its monolayer, in sharp contrast to its bulk counterpart, which is paramagnetic. Similarly, room temperature magnetic ordering was discovered in metallic Fe$_3$GeTe$_2$ crystals by employing the ionic gating technique. The use of room-temperature 2D magnets for potential spintronic applications is further enabled by their growth using molecular beam epitaxy techniques down to monolayer thickness, as demonstrated for MnSe$_2$ (O’Hara et al., 2018). Room temperature spintronic devices could integrate the spin transport properties of graphene with the memory of the 2D magnet, exploiting proximity-induced magnetization by the 2D magnet into graphene as demonstrated via the proximity anisotropic magnetoresistance effect in graphene/CrBr$_3$ heterostructures (Ghazaryan et al., 2018). Recent observation of defect-induced long-range magnetism in air-stable, metallic PtSe$_2$ (Aysar et al., 2019) and semiconducting MoTe$_2$ (Guguchia et al., 2018) expands the range of 2D magnets into materials that are intrinsically nonmagnetic and would otherwise be overlooked. The emerging mix of experimental techniques and new materials, and the resulting new effects like gate-tunable magnetism, creates exciting prospects for 2D-based voltage-controlled magnetoelectronics.

IV. FINAL REMARKS

Since the first demonstration of spin transport in graphene (Tombros et al., 2007) we have seen a remarkable progress in 2D-based spintronics, including graphene related materials, getting tantalisingly close towards practical applications. This includes, but is not limited to: a two orders of magnitude enhancement in graphene spin lifetime (Droegeler et al., 2016), high quality spin transport in large-scale graphene (Aysar et al., 2011; Gebeyehu et al., 2019; Kamalakar et al., 2015), gate-induced spin manipulation in 2D semiconductors (Aysar et al., 2017a) and graphene/TMDC heterostructures (Dankert and Dash, 2017; Yan et al., 2016), proximity induced spin-to-charge conversion in graphene/TMDC heterostructures (Ghiasi et al., 2019; Li et al., 2019; Safeer et al., 2019), and the recent discovery of 2D magnets which can even remain magnetically ordered down to a few atoms thick at room temperature (Deng et al., 2018). However, there are long-standing challenges that need to be addressed for exploiting the full potential of 2D spintronics applications. There is still room for improving spin lifetime and spin relaxation length by studying fully encapsulated, high mobility graphene spin valves.
We believe there are two major breakthroughs expected when these devices reach the electronic quality of state of art charge-based devices. First, experimental results in such high-quality spintronic devices will guide the theory to convincingly identify the limiting spin relaxation mechanisms. Second, analogous to the demonstration of micrometer-scale ballistic charge transport at room temperature (Mayorov et al., 2011), the realization of ballistic spin transport at room temperature could open a whole new range of opportunities, both in terms of applications, and in developing the theoretical description to interpret the role of device geometry, spin precession, and transport in a regime beyond the diffusive approximation. Considering the field started only over a decade ago, and its current progress, the vision of low-power all-spin-logic devices based on 2D van der Waal heterostructures seems within the reach of the next decade.

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